

REMARKS

Claims 1-13 are pending in the application, with claims 1, 4, 7 and 11 being independent. The title and claims 1, 4, 7 and 11 have been amended. No new matter has been added.

In particular, each of claims 1 and 4 has been amended to recite that the second conductive layer pattern is formed by etching after recessing an edge of the mask pattern remaining on the first conductive layer pattern, and each of claims 7 and 11 has been amended to recite that a first conductive layer pattern is formed by etching after performing plasma treatment to decrease the taper angle of an edge of the mask pattern. Support for the amendment to claims 1 and 4 may be found, for example, in Fig. 1D and the accompanying text, and support for the amendment to claims 7 and 11 may be found, for example, in Fig. 5B and the accompanying text. In addition, each of the independent claims has been amended to clarify that the gate insulating film is between the semiconductor layer and the conductive layers.

The amendment to the title is believed to address the Examiner's objection.

Claims 1-13 have been rejected as being anticipated by Yamazaki (US2002/0158288). With respect to claims 1 and 4, and their dependent claims, applicant requests reconsideration and withdrawal of the rejection because Yamazaki does not describe or suggest forming a second conductive layer pattern after recessing the edge of a mask pattern, as recited in each of claims 1 and 4. Instead, the reduction in size of, for example, the mask pattern 110 from Fig. 1B to Fig. 1C appears to result from the second etching processing (i.e., the reduction in the size of the mask occurs as a result of the second etching process rather than before the second etching process). See Yamazaki at paragraph 0088.

With respect to claims 7 and 11, and their dependent claims, applicant requests reconsideration and withdrawal of the rejection because Yamazaki does not describe or suggest forming a first conductive layer pattern after performing plasma treatment to decrease the taper angle of an edge of the mask pattern, as recited in each of claims 7 and 11. While Yamazaki describes inductively coupled plasma etching as a process used in etching the conductive films in

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paragraph 0083, Yamazaki does not describe or suggest using plasma treatment "to decrease the taper angle of an edge of the mask pattern."

Applicant submits that all claims are in condition for allowance.

Enclosed is a \$120 check for the Petition for Extension of Time fee. Please apply any other charges or credits to deposit account 06-1050.

Respectfully submitted,


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